FAM65HR51DS1

Table 4. ELECTRICAL SPECIFICATIONS (T_J = 25 C, Unless Otherwise Specified)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
BV_{DSS}	Drain−to−Source Breakdown Voltage	I_D = 1 mA, V_{GS} = 0 V	650	−	−	V
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 3.3 mA	3.0	−	5.0	V
$R_{DS(ON)}$	Q1 – Q4 MOSFET On Resistance	V_{GS} = 10 V, I_D = 20 A	−	44	51	mΩ
$R_{DS(ON)}$	Q1 – Q4 MOSFET On Resistance	V_{GS} = 10 V, I_D = 20 A, T_J = 125 C (Note 4)	−	79	−	mΩ
g_{FS}	Forward Transconductance	V_{DS} = 20 V, I_D = 20 A (Note 4)	−			

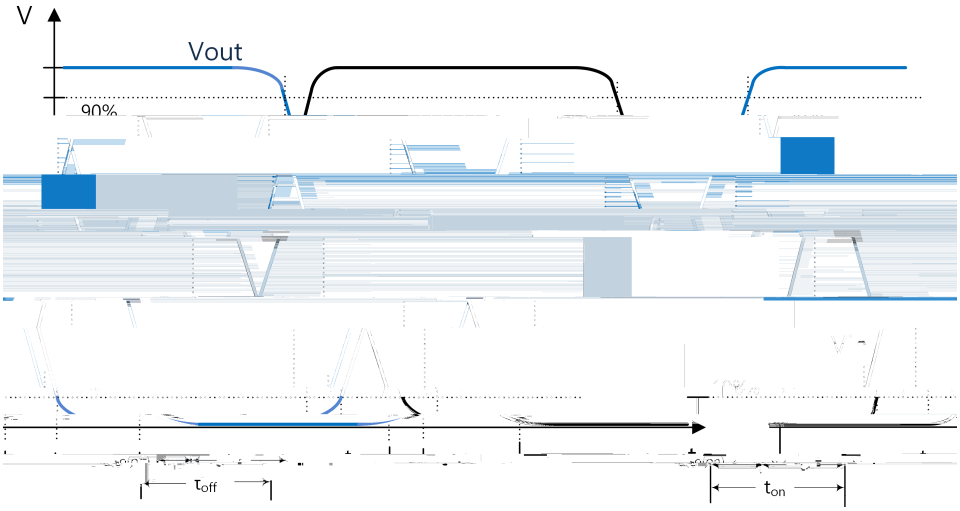

Figure 3. Timing Measurement Variable Definition

Table 7. PARAMETER OF SWITCHING CHARACTERISTICS

Turn−On Delay ($t_{d(on)}$)	This is the time needed to charge the input capacitance, Ciss, before the load current ID starts flowing. The measurement conditions are described in the Table 4. For signal definition please check Figure 3 above.
Rise Time (t_r)	The rise time is the time to discharge output capacitance, Coss. After that time the MOSFET conducts the given load current ID. The measurement conditions are described in the Table 4. For signal definition please check Figure 3 above.

Turn−On Time (t

TYPICAL CHARACTERISTICS

Figure 4. Normalized Power Dissipation vs. Case

Figure 5. Maximum Continuous I_D vs. Case

TYPICAL CHARACTERISTICS

Figure 10. On−Resistance vs. Gate−to−Source

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